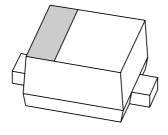
## DISCRETE SEMICONDUCTORS

# DATA SHEET



## BAP65-01 Silicon PIN diode

Preliminary specification

2001 Nov 01





## Silicon PIN diode BAP65-01

#### **FEATURES**

- High voltage, current controlled
- RF resistor for RF switches
- Low diode capacitance
- Low diode forward resistance (low loss)
- Very low series inductance.

## **APPLICATIONS**

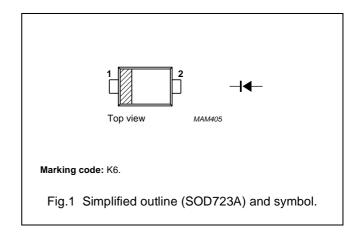
- · RF attenuators and switches
- · Bandswitch for TV tuners
- Series diode for mobile communication transmit/receive switch.

## **DESCRIPTION**

Planar PIN diode in a SOD723A ultra small SMD plastic package.

### **PINNING**

PIN	DESCRIPTION
1	cathode
2	anode



## **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_R$	continuous reverse voltage		_	30	V
I <sub>F</sub>	continuous forward current		_	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>s</sub> ≤ 90 °C	_	315	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		-65	+150	°C

Philips Semiconductors Preliminary specification

Silicon PIN diode BAP65-01

## **ELECTRICAL CHARACTERISTICS**

 $T_i = 25$  °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 50 mA	0.9	1.1	V
I <sub>R</sub>	reverse leakage current	V <sub>R</sub> = 20 V	_	20	nA
C <sub>d</sub> diode ca	diode capacitance	V <sub>R</sub> = 0 V; f = 1 MHz	0.61	_	pF
		V <sub>R</sub> = 1 V; f = 1 MHz	0.48	0.9	pF
		V <sub>R</sub> = 3 V; f = 1 MHz	0.43	0.8	pF
		V <sub>R</sub> = 20 V; f = 1 MHz	0.375	_	pF
r <sub>D</sub>	diode forward resistance	$I_F = 1 \text{ mA}; f = 100 \text{ MHz}$	1.0	_	Ω
		$I_F = 5 \text{ mA}$ ; $f = 100 \text{ MHz}$ ; note 1	0.6	0.95	Ω
		I <sub>F</sub> = 10 mA; f = 100 MHz; note 1	0.5	0.9	Ω
		$I_F = 100 \text{ mA}$ ; $f = 100 \text{ MHz}$	0.3	_	Ω
S <sub>21</sub>   <sup>2</sup>	isolation	V <sub>R</sub> = 0; f = 900 MHz	9.4	_	dB
		$V_R = 0$ ; $f = 1800 \text{ MHz}$	5.5	_	dB
		$V_R = 0$ ; $f = 2450 \text{ MHz}$	4.1	_	dB
S <sub>21</sub>   <sup>2</sup>	insertion loss	$I_F = 1 \text{ mA}; f = 900 \text{ MHz}$	0.10	_	dB
		$I_F = 1 \text{ mA}; f = 1800 \text{ MHz}$	0.12	_	dB
		$I_F = 1 \text{ mA}$ ; $f = 2450 \text{ MHz}$	0.15	_	dB
$ s_{21} ^2$	insertion loss	$I_F = 5 \text{ mA}; f = 900 \text{ MHz}$	0.08	_	dB
		$I_F = 5 \text{ mA}$ ; $f = 1800 \text{ MHz}$	0.10	_	dB
		$I_F = 5 \text{ mA}$ ; $f = 2450 \text{ MHz}$	0.12	_	dB
S <sub>21</sub>   <sup>2</sup>	insertion loss	$I_F = 10 \text{ mA}; f = 900 \text{ MHz}$	0.06	_	dB
		I <sub>F</sub> = 10 mA; f = 1800 MHz	0.09	_	dB
		I <sub>F</sub> = 10 mA; f = 2450 MHz	0.11	_	dB
S <sub>21</sub>   <sup>2</sup>	insertion loss	I <sub>F</sub> = 100 mA; f = 900 MHz	0.05	_	dB
		I <sub>F</sub> = 100 mA; f = 1800 MHz	0.08	_	dB
		I <sub>F</sub> = 100 mA; f = 2450 MHz	0.10	_	dB
τ∟	charge carrier life time	when switched from $I_F$ = 10 mA to $I_R$ = 6 mA; $R_L$ = 100 $\Omega$ ; measured at $I_R$ = 3 mA	0.17	_	μs
L <sub>S</sub>	series inductance	I <sub>F</sub> = 100 mA; f = 100 MHz	0.6	_	nH
	•	•			

## Note

1. Guaranteed on AQL basis: inspection level S4, AQL 1.0.

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R <sub>th j-s</sub>	thermal resistance from junction to soldering point	190	K/W

## Silicon PIN diode BAP65-01

#### **GRAPHICAL DATA**

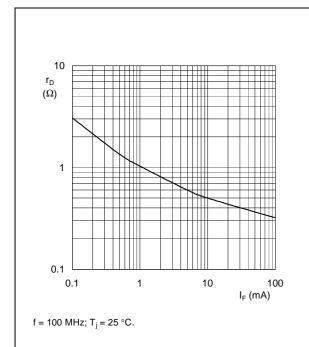


Fig.2 Forward resistance as a function of forward current; typical values.

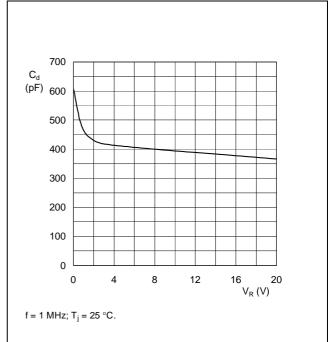
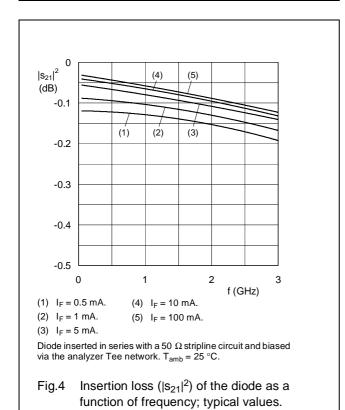
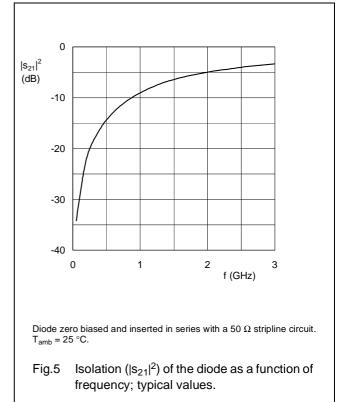


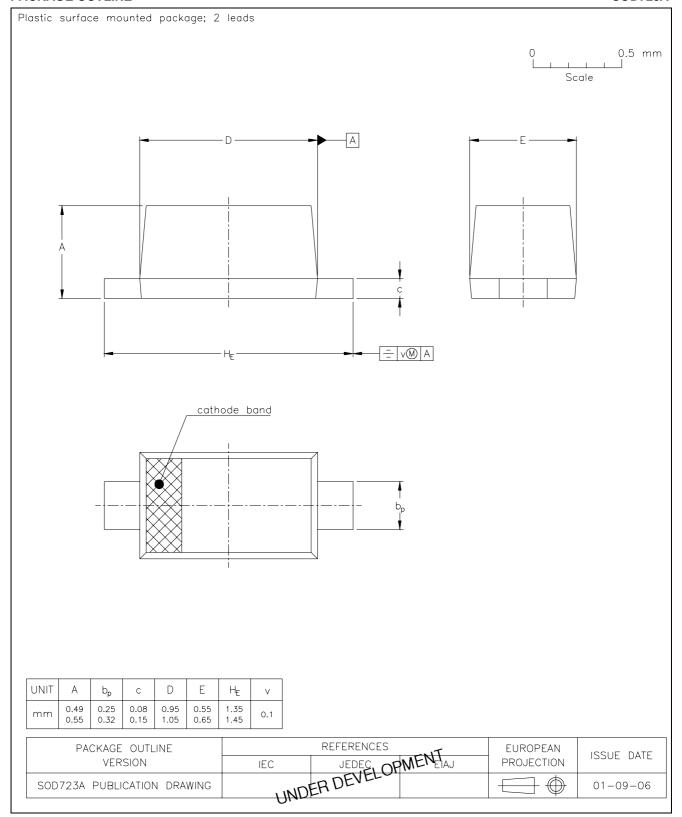
Fig.3 Diode capacitance as a function of reverse voltage; typical values.





## Silicon PIN diode BAP65-01

## PACKAGE OUTLINE SOD723A



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Silicon PIN diode BAP65-01

#### **DATA SHEET STATUS**

DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITIONS
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